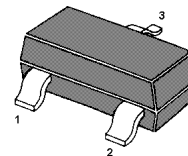


BC856...BC860

PNP Silicon Epitaxial Transistor

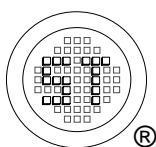
for switching and amplifier applications



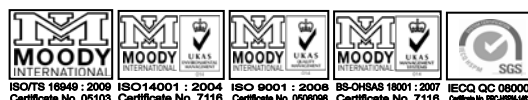
1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	BC856	$-V_{CBO}$	80	V
	BC857, BC860	$-V_{CBO}$	50	V
	BC858, BC859	$-V_{CBO}$	30	V
Collector Emitter Voltage	BC856	$-V_{CEO}$	65	V
	BC857, BC860	$-V_{CEO}$	45	V
	BC858, BC859	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V	
Collector Current	$-I_C$	100	mA	
Peak Collector Current	$-I_{CM}$	200	mA	
Power Dissipation	P_{tot}	200	mW	
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$	



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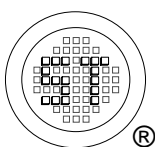


Dated: 08/08/2012 Rev: 01

BC856...BC860

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	Current Gain Group A	h_{FE}	125	250	-
	B	h_{FE}	220	475	-
	C	h_{FE}	420	800	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	15	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	BC856	$-V_{(BR)CBO}$	80	-	V
	BC857, BC860	$-V_{(BR)CBO}$	50	-	V
	BC858, BC859	$-V_{(BR)CBO}$	30	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	BC856	$-V_{(BR)CES}$	80	-	V
	BC857, BC860	$-V_{(BR)CES}$	50	-	V
	BC858, BC859	$-V_{(BR)CES}$	30	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	BC856	$-V_{(BR)CEO}$	65	-	V
	BC857, BC860	$-V_{(BR)CEO}$	45	-	V
	BC858, BC859	$-V_{(BR)CEO}$	30	-	V
Emitter Base Breakdown Voltage at $-I_E = 1\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V	
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V	
	$-V_{CE(sat)}$	-	0.65	V	
Base Emitter On Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE(on)}$	0.6	0.75	V	
	$-V_{BE(on)}$	-	0.82	V	
Current Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF	



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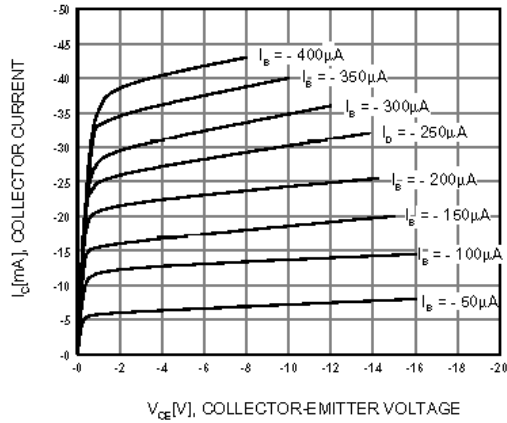


Figure 1. Static Characteristic

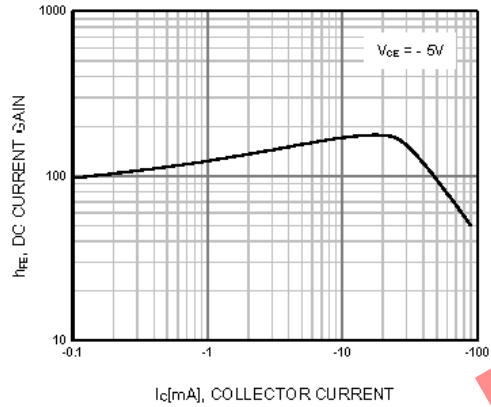


Figure 2. DC current Gain

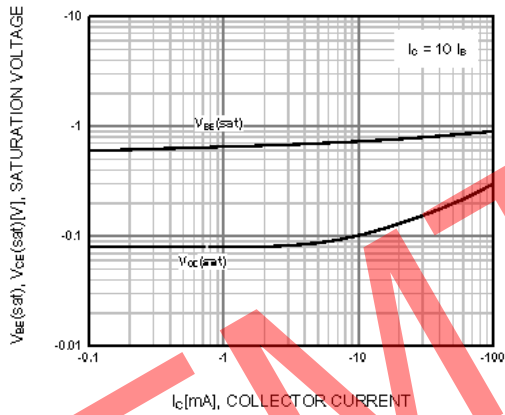


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

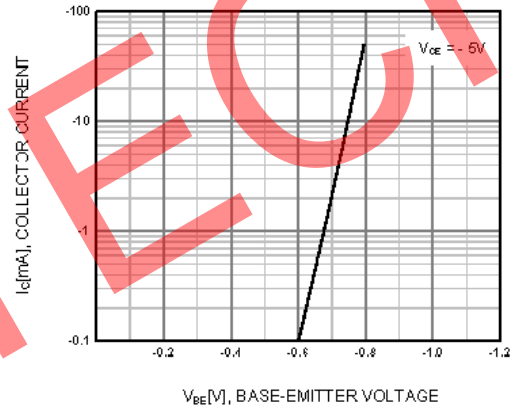


Figure 4. Base-Emitter On Voltage

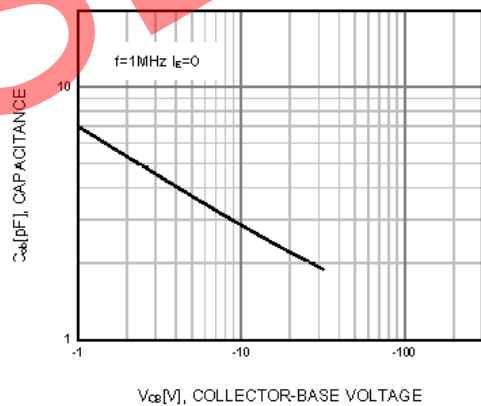


Figure 5. Collector Output Capacitance

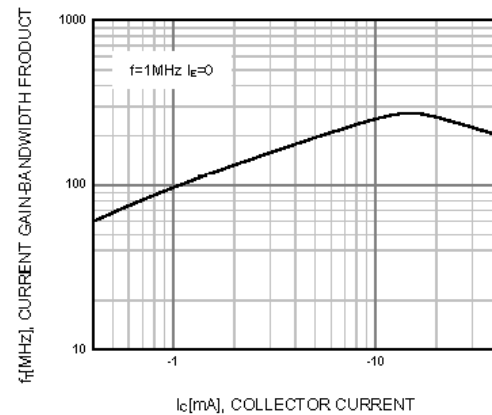


Figure 6. Current Gain Bandwidth Product

